

Apurba Laha

List of Publications by Year in descending order

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32
papers

234
citations

1040056

9
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14
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32
all docs

32
docs citations

32
times ranked

248
citing authors

#	ARTICLE	IF	CITATIONS
1	Growth of uniform Mg-doped p-AlGa _N nanowires using plasma-assisted molecular beam epitaxy technique for UV-A emitters. <i>Nanotechnology</i> , 2022, 33, 384001.	2.6	3
2	Carrier-Induced Defect Saturation in Green InGa _N LEDs: A Potential Phenomenon to Enhance Efficiency at Higher Wavelength Regime. <i>ACS Photonics</i> , 2021, 8, 926-932.	6.6	13
3	Impact of Ex-Situ Heating on Carrier Kinetics in GaN/InGa _N Based Green LEDs. <i>ECS Journal of Solid State Science and Technology</i> , 2021, 10, 035004.	1.8	3
4	Epi-Gd ₂ O ₃ /AlGa _N /Ga _N MOSHEMT: A Potential Solution Toward Leveraging the Application of AlGa _N /Ga _N /Si HEMT With Improved ON/OFF Operating at 473 K. <i>IEEE Transactions on Electron Devices</i> , 2021, 68, 2653-2660.	3.0	6
5	A Highly Sensitive and Robust GaN Ultraviolet Photodetector Fabricated on 150-mm Si (111) Wafer. <i>IEEE Transactions on Electron Devices</i> , 2021, 68, 2796-2803.	3.0	11
6	Unraveling the Quality of the Active Region in GaN/InGa _N Green LEDs Using Capacitance-Voltage Measurements. , 2021, , .		1
7	Defect Saturation with Carriers in GaN/InGa _N LEDs: A potential phenomenon to confront the green gap. , 2021, , .		0
8	Decomposition Resilience of GaN Nanowires, Crested and Surficially Passivated by AlN. <i>Crystal Growth and Design</i> , 2020, 20, 4867-4874.	3.0	9
9	Role of defect saturation in improving optical response from InGa _N nanowires in higher wavelength regime. <i>Nanotechnology</i> , 2020, 31, 495705.	2.6	11
10	Ultra high-sensitive, prompt response and recovering Pt/(Pt+SiO ₂) cermet layer/GaN-based hydrogen sensor for life-saving applications. <i>Nanotechnology</i> , 2020, 31, 46LT02.	2.6	1
11	Effect of Thermal Management on the Performance of VCSELs. <i>IEEE Transactions on Electron Devices</i> , 2020, 67, 3736-3739.	3.0	9
12	Epi-Gd ₂ O ₃ /AlGa _N /Ga _N MOS HEMT on 150-µm Si wafer: A fully epitaxial system for high power application. <i>Applied Physics Letters</i> , 2019, 115, 063502.	3.3	14
13	Efficient ab initio plus analytic calculation of the effect of GaN layer tensile strain in AlGa _N /Ga _N heterostructures. <i>Japanese Journal of Applied Physics</i> , 2019, 58, 094001.	1.5	6
14	Critical analysis of micro-thermogravimetry of CuSO ₄ ·5H ₂ O crystals using heatable microcantilevers. <i>Journal of Micromechanics and Microengineering</i> , 2019, 29, 105009.	2.6	2
15	Study of surface over-layer contribution to Dislocation Assisted Tunneling current: Strategy to improve Pt/n-GaN Schottky characteristics. <i>Materials Research Express</i> , 2019, 6, 105917.	1.6	0
16	Self-Assembled Sn Nanocrystals as the Floating Gate of Nonvolatile Flash Memory. <i>ACS Applied Electronic Materials</i> , 2019, 1, 1852-1858.	4.3	8
17	Triaxially uniform high-quality Al _x Ga _{1-x} N (x ≈ 50%) nanowires on template free sapphire substrate. <i>Nanotechnology</i> , 2019, 30, 065603.	2.6	6
18	Engineering V-shaped pits in InGa _N layers grown by PA-MBE toward optimizing the active region of green LEDs. <i>Journal of the Optical Society of America B: Optical Physics</i> , 2019, 36, 616.	2.1	10

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19	Excimer laser annealing: An alternative route and its optimisation to effectively activate Si dopants in AlN films grown by plasma assisted molecular beam epitaxy. <i>Materials Research Bulletin</i> , 2018, 97, 300-305.	5.2	9
20	Effect of nitridation time on structural, optical and electrical properties of InN films grown on c-sapphire substrates by PAMBE. <i>Journal of Materials Science: Materials in Electronics</i> , 2018, 29, 3927-3934.	2.2	0
21	Wafer-scale all-epitaxial GeSn-on-insulator on Si(111) by molecular beam epitaxy. <i>Journal Physics D: Applied Physics</i> , 2018, 51, 32LT01.	2.8	2
22	Superconductivity in epitaxial InN thin films with large critical fields. <i>AIP Conference Proceedings</i> , 2018, , .	0.4	1
23	Molecular beam epitaxy and defect structure of Ge (111)/epi-Gd ₂ O ₃ (111)/Si (111) heterostructures. <i>Journal of Applied Physics</i> , 2018, 124, .	2.5	9
24	Tuning the effective band gap and finding the optimal growth condition of InN thin films on GaN/sapphire substrates by plasma assisted molecular beam epitaxy technique. <i>Superlattices and Microstructures</i> , 2017, 101, 405-414.	3.1	8
25	On the correlation of growth, structural and electrical properties of epitaxial Ge grown on Si by solid source molecular beam epitaxy. <i>Current Applied Physics</i> , 2017, 17, 327-332.	2.4	4
26	Epitaxial Gd ₂ O ₃ on GaN and AlGaN: a potential candidate for metal oxide semiconductor based transistors on Si for high power application. <i>Journal Physics D: Applied Physics</i> , 2017, 50, 475102.	2.8	4
27	Piezoresponse force microscopy (PFM) characterization of GaN nanowires grown by Plasma assisted Molecular beam epitaxy (PA-MBE). , 2016, , .		3
28	Improved Ohmic contact to GaN and AlGaN/GaN two-dimensional electron gas using trap assisted tunneling by B implantation. <i>Physica Status Solidi (B): Basic Research</i> , 2015, 252, 989-995.	1.5	10
29	Impact of GaN buffer layer thickness on structural and optical properties of AlGaN/GaN based high electron mobility transistor structure grown on Si(111) substrate by plasma assisted molecular beam epitaxy technique. , 2015, , .		2
30	Effective control on flat band voltage of epitaxial lanthanide oxide based metal oxide semiconductor capacitors by interfacial carbon. <i>Applied Physics Letters</i> , 2013, 102, .	3.3	7
31	Epitaxial Gd ₂ O ₃ on strained Si _{1-x} Ge _x layers for next generation complementary metal oxide semiconductor device application. <i>Applied Physics Letters</i> , 2013, 103, 153501.	3.3	8
32	Impact of Si substrate orientations on electrical properties of crystalline Gd ₂ O ₃ thin films for high-K application. <i>Applied Physics Letters</i> , 2006, 89, 143514.	3.3	54